



SOT-23-3L Plastic-Encapsulated Transistors

2SA812 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM} : 0.2 \text{ W (Tamb=25°C)}$$

Collector current

$$I_{CM} : -0.1 \text{ A}$$

Collector-base voltage

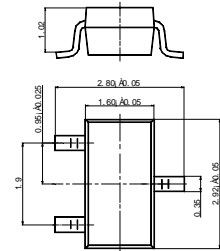
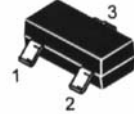
$$V_{(BR)CBO} : -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	90		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
Base-emitter voltage	V_{BE}	$I_C = -1\text{mA}, V_{CE} = -6\text{V}$			-0.68	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -10\text{mA}$	180			MHz

CLASSIFICATION OF h_{FE}

Marking	M4	M5	M6	M7
Range	90-180	135-270	200-400	300-600